

(730C Heater 200Torr 70sccm SiH<sub>4</sub>; Std Pplate)

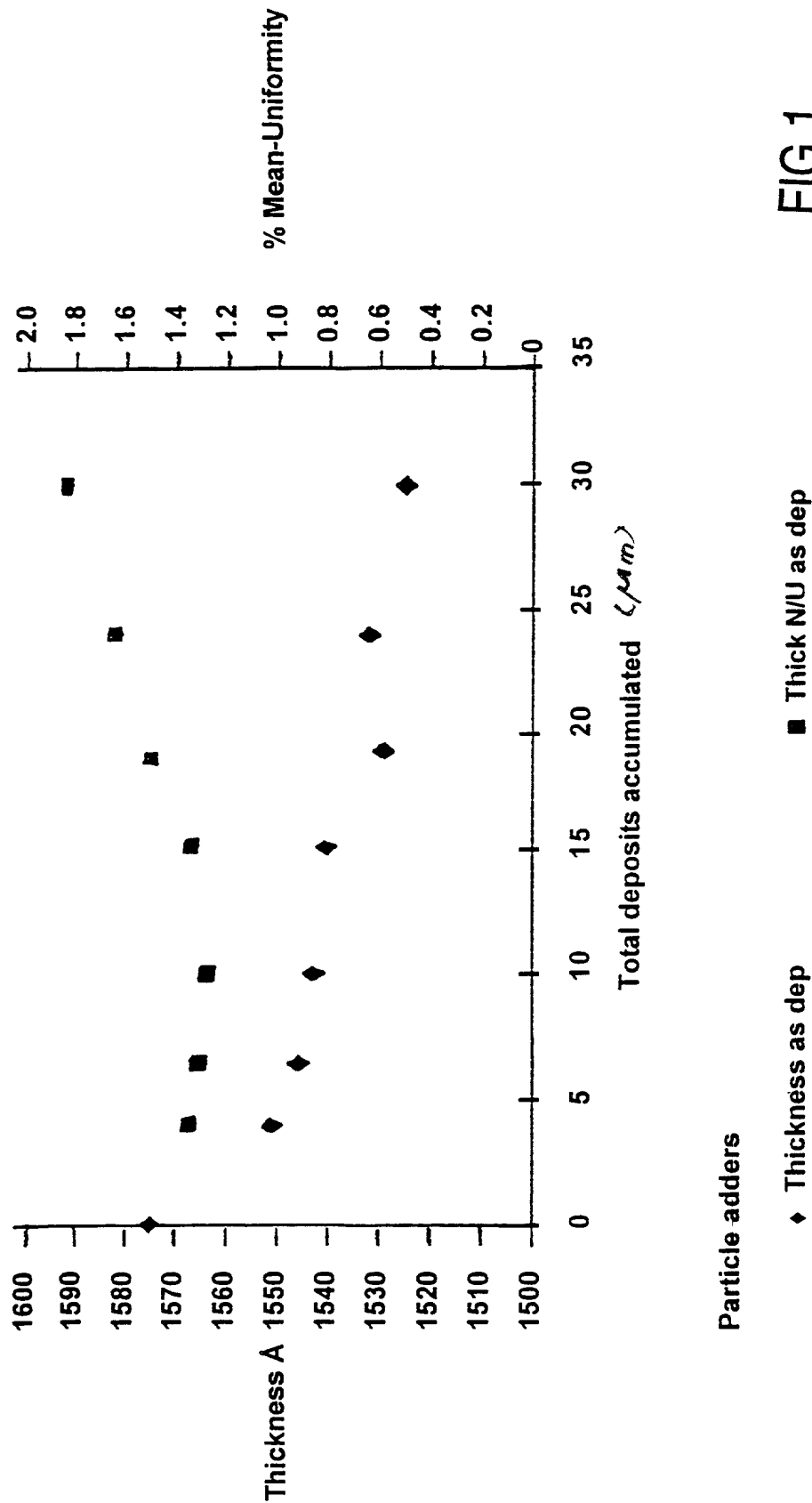
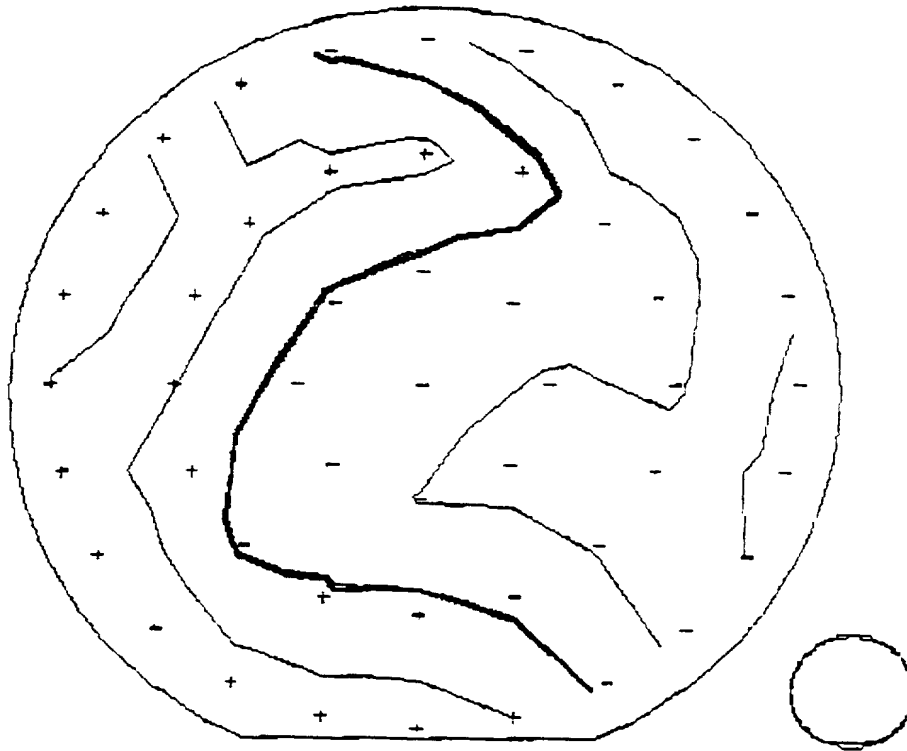


FIG.1

2/15



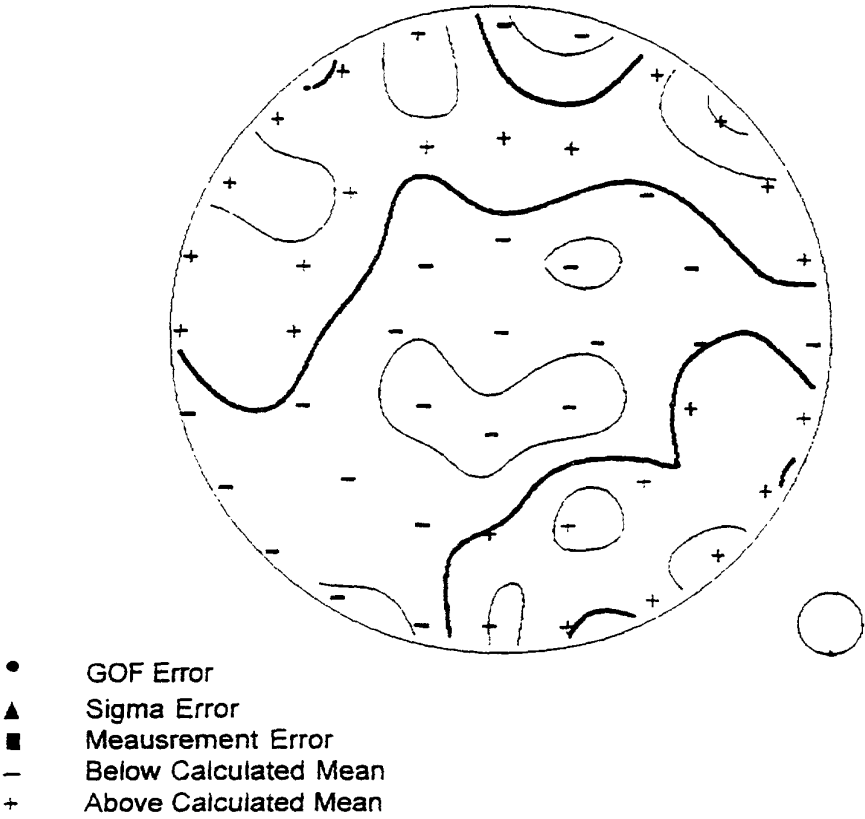
MEAN 1138.6  
STD DEV 15.597 1.370%  
MINIMUM 1111.1  
MAXIMUM 1172.4  
# SITES/GOOD 49/49

WAFER DIAM 200.00  
TEST DIAM 194.00  
TEMPLATE MAP 49 SITE  
CONTOUR DISP STD  
INTERVAL 1.000

SUBSTRATE 50MM (275  $\mu$ ) Si  
SORTING SIGMA 3.0  
CORRELATION \* NONE  
UNITS ANGSTROMS

LAYER 2 FILM POLY Si  
MEAN-TARGET 0.000  
WARNING 0.000  
SPEC 0.000

FIG.2



Wafer Diameter 200 mm  
Edge Exclusion 3.000 mm  
Type/Pattern Polar/49 Site Map  
# Sites/Good 49/49  
Measurement 2<sup>nd</sup> Thickness  
Mean 1318.29 Å  
Std. Deviation 10.5104 Å / 0.797%  
Minimum 1300.49 Å  
Maximum 1341.45 Å  
Range 40.95

Limits: Percent  
Mean Target 0.00 Å  
U/L Control 20.0%/20.0%  
U/L Warning 5.0%/5.0%  
U/L Sigma 3.00/3.00  
Stdv Control 1.000  
Contour Display Percent  
Interval 11.0962

Film Stack Ox/aSi/Ox-T, T&n&k,  
T Copy  
Layer 3 Thermal SiO2  
Layer 2 # Amorphous Si  
Layer 1 Thermal SiO2  
Substrate Silicon

FIG.3

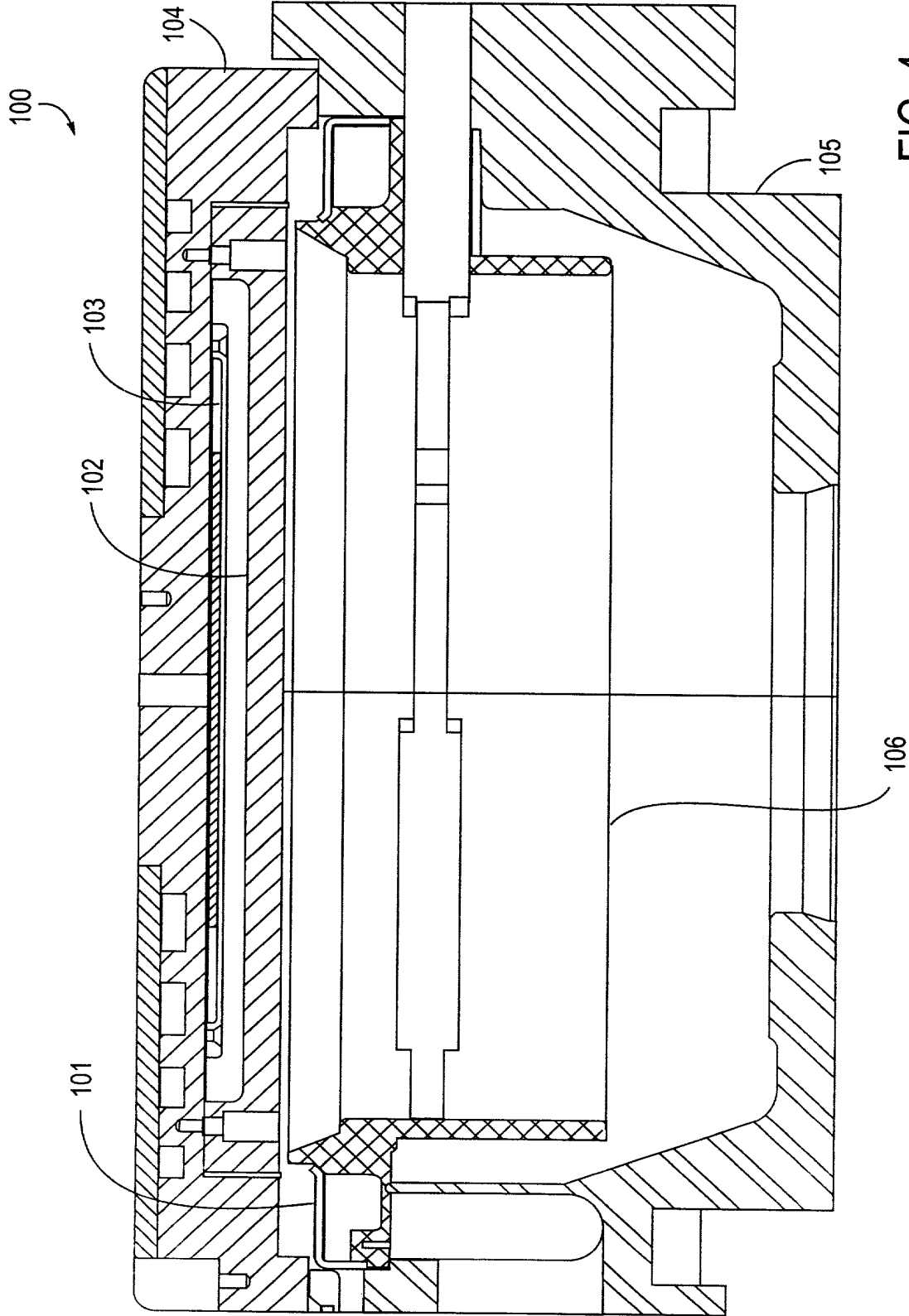


FIG. 4

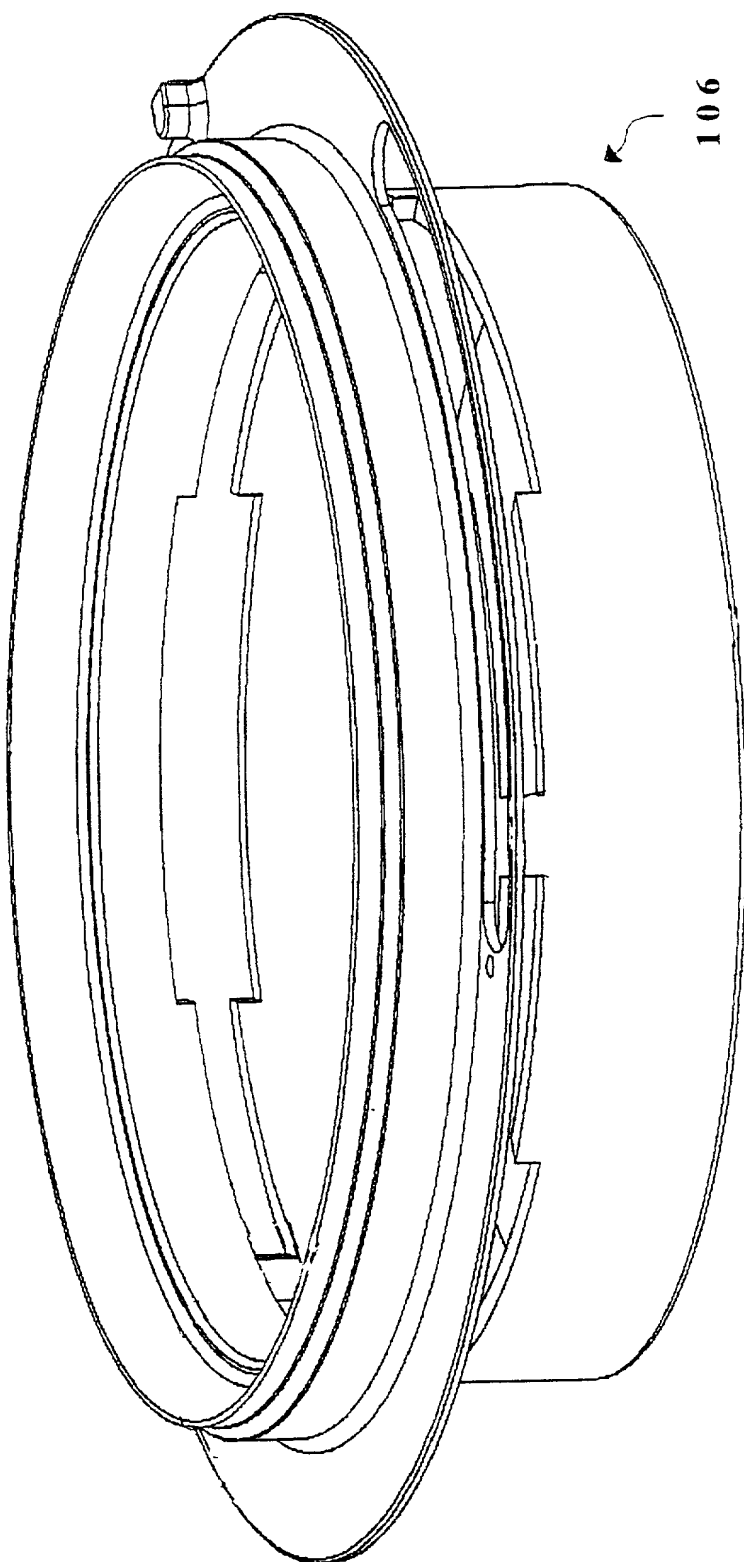


FIG.5

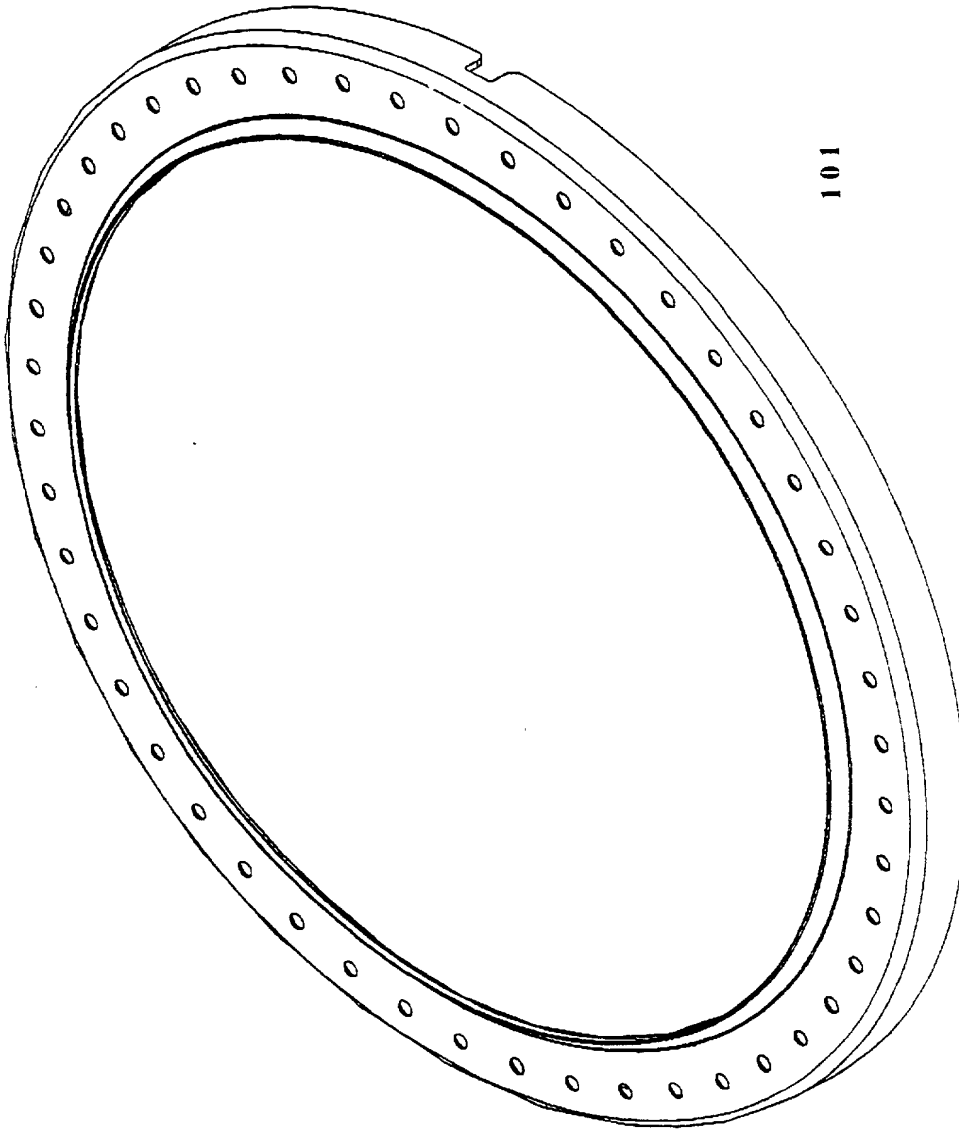


FIG.6

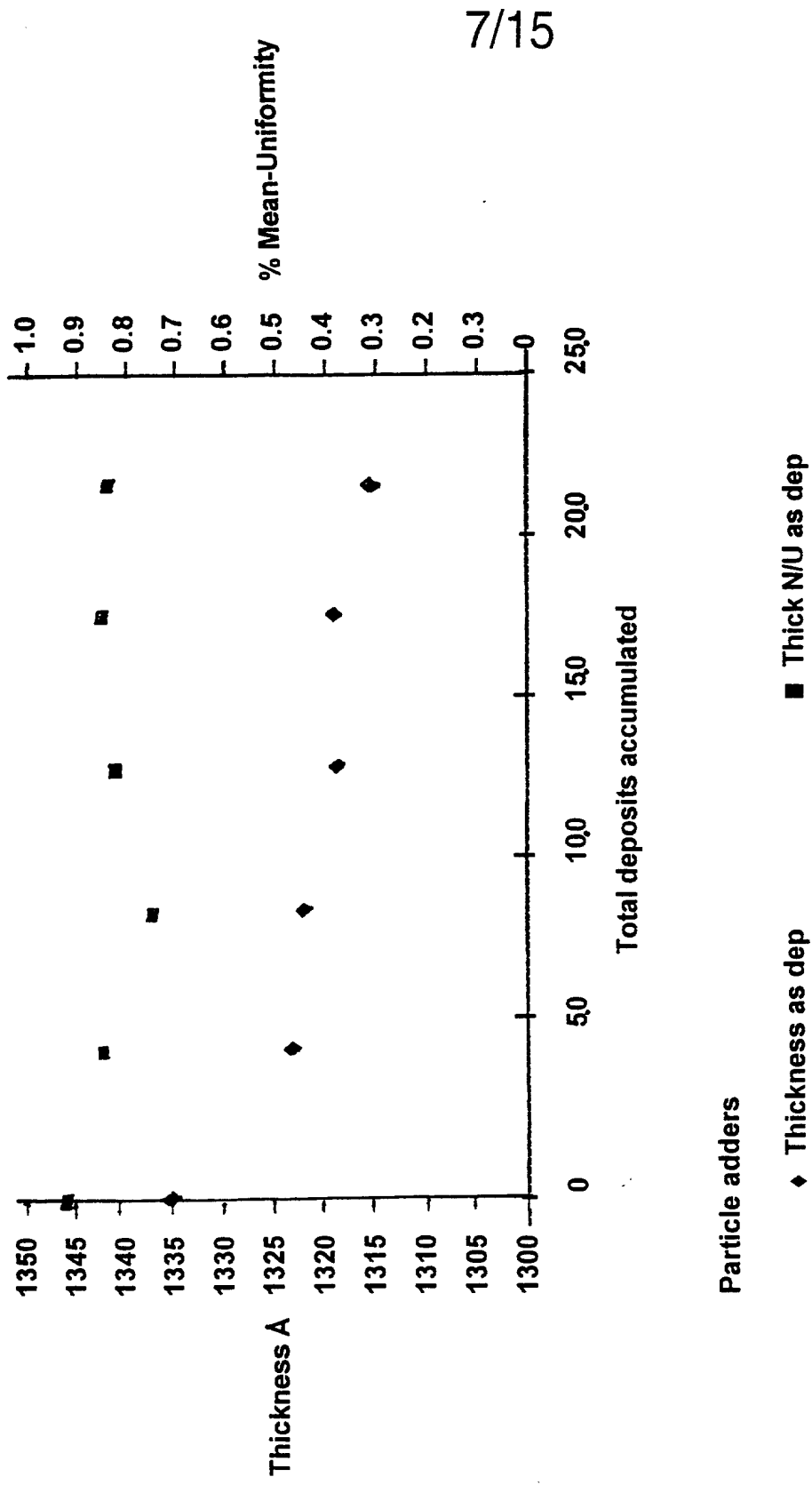


FIG.7

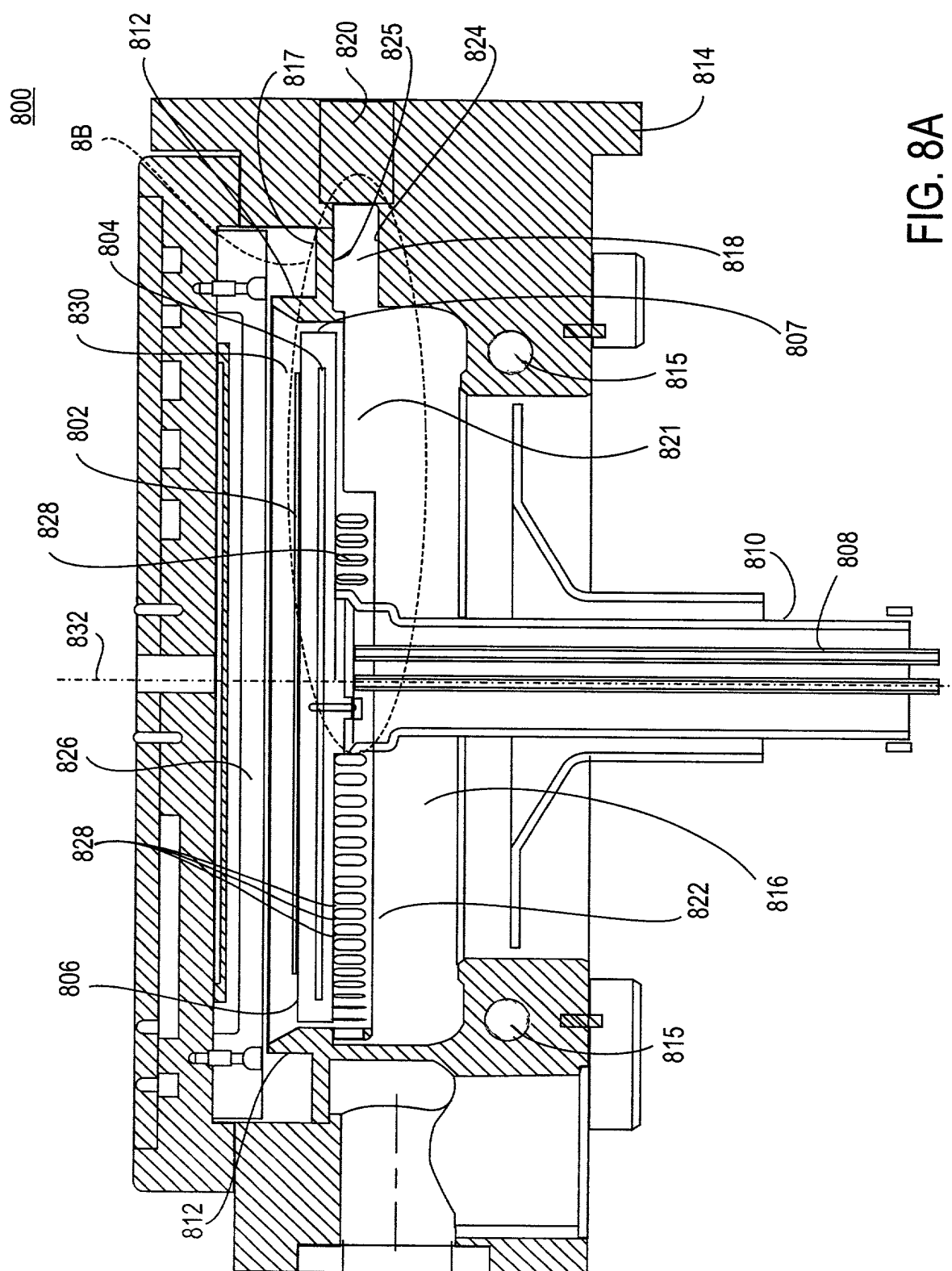


FIG. 8A



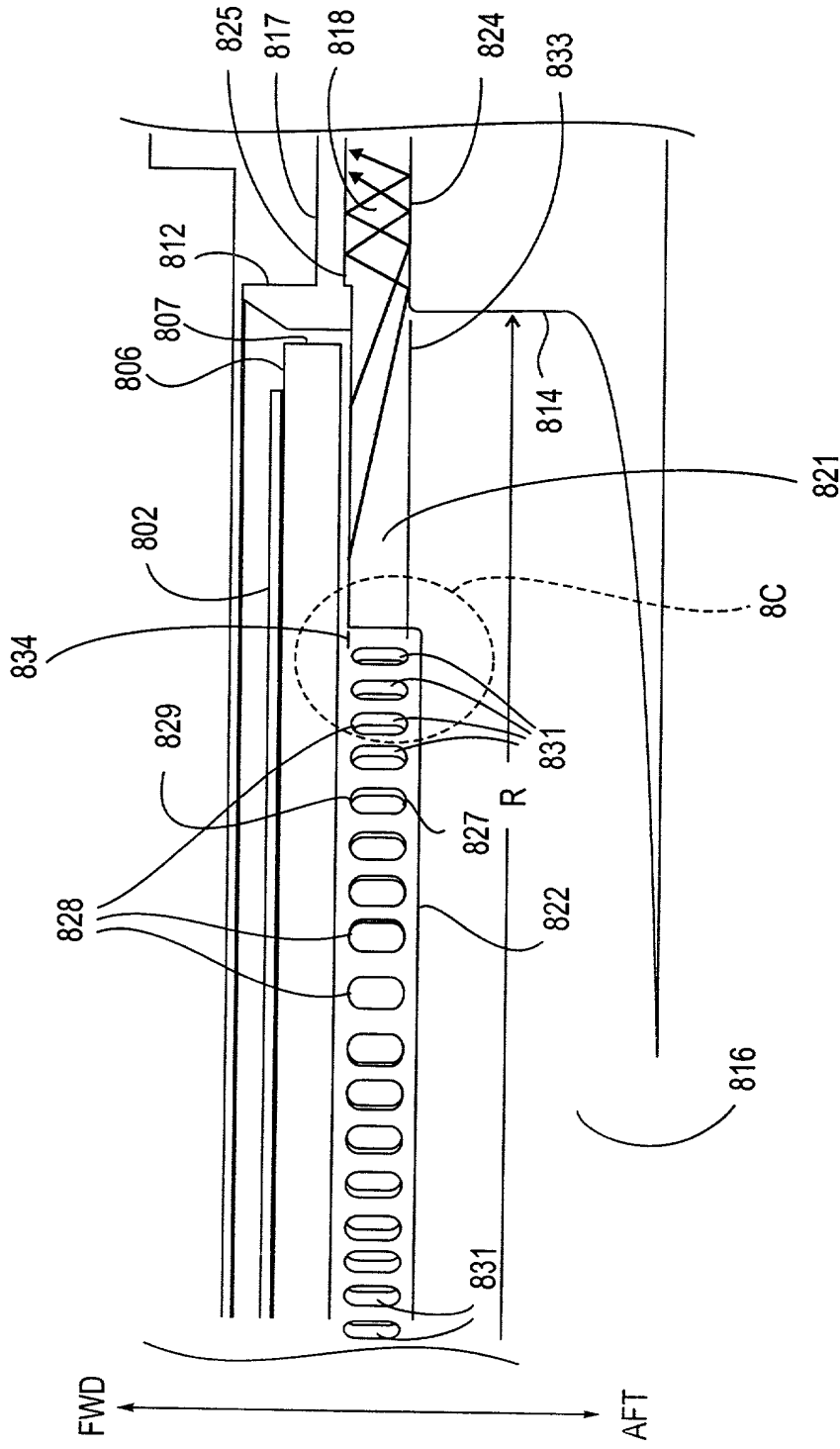


FIG. 8B

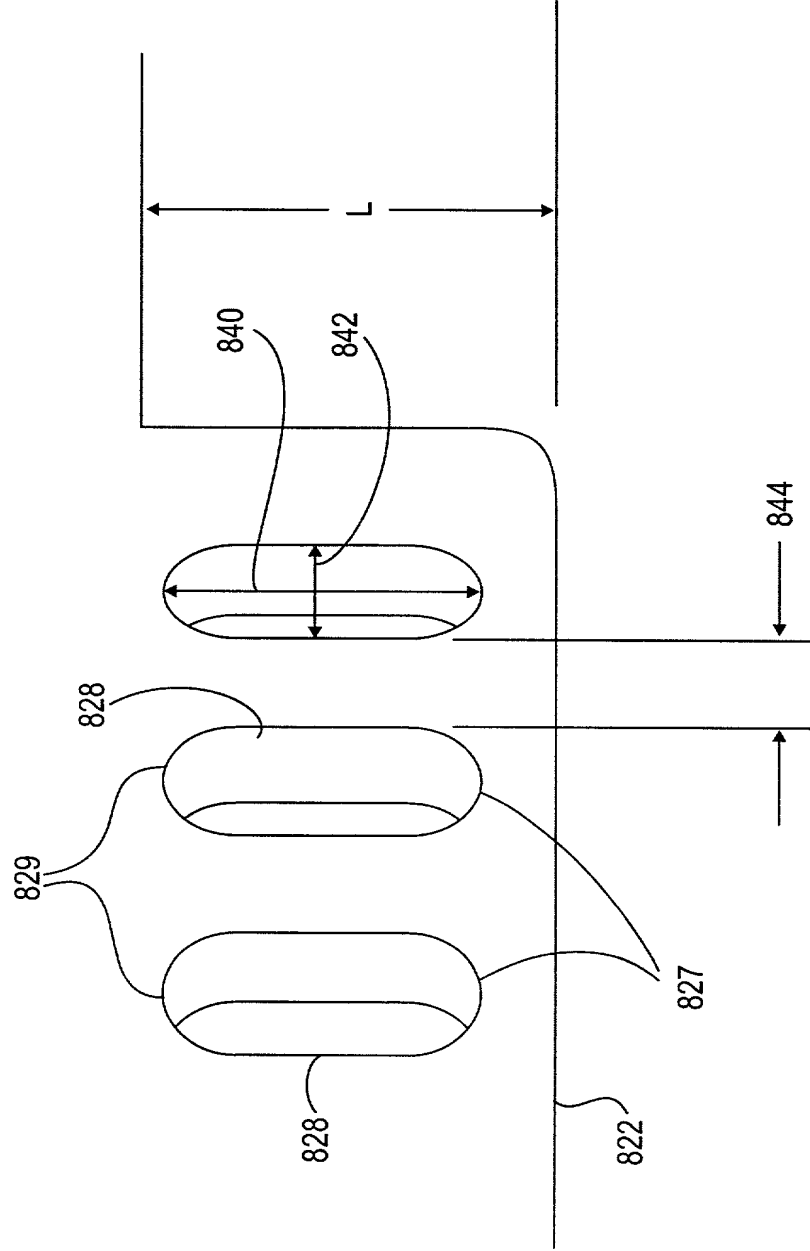


FIG. 8C

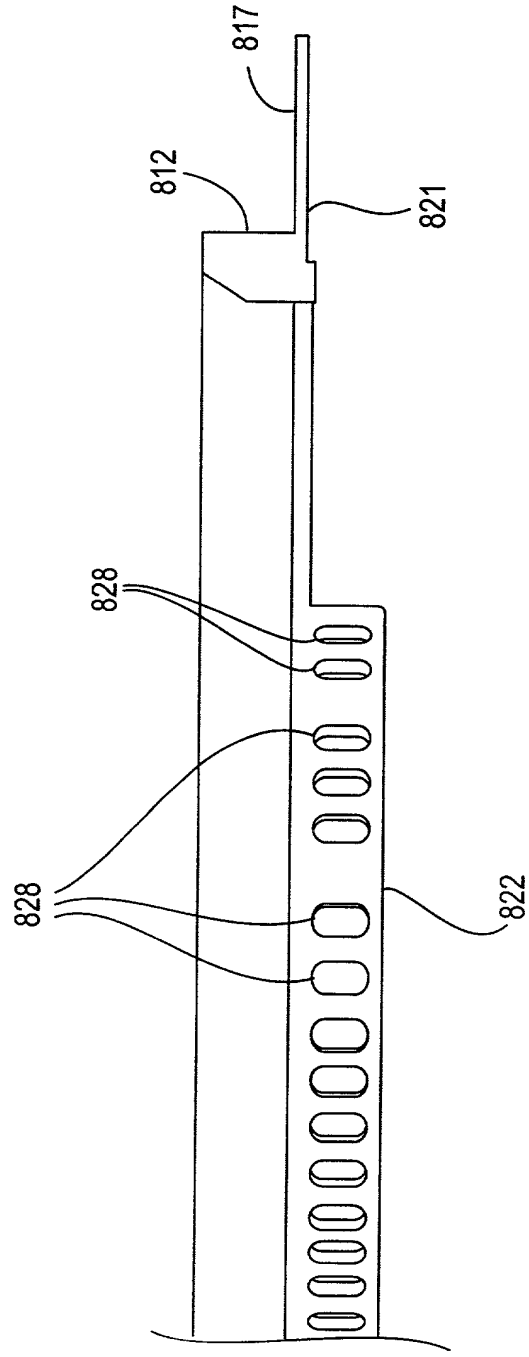


FIG. 8D

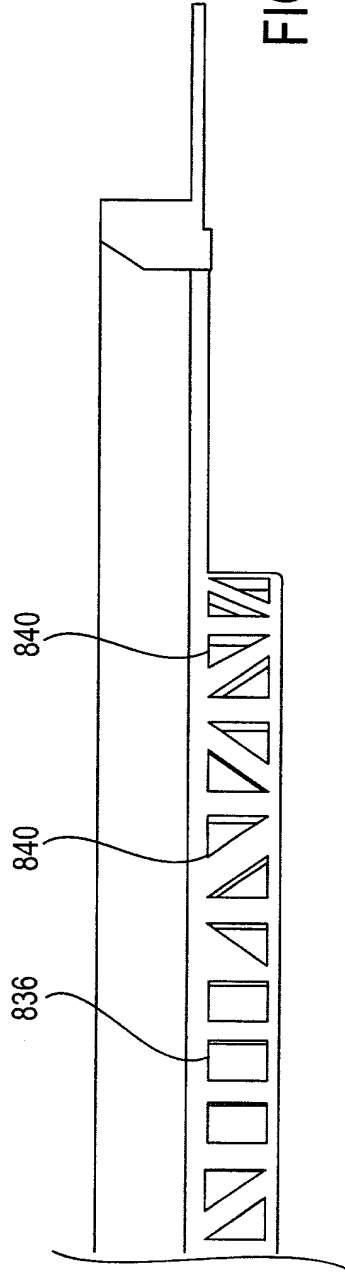


FIG. 8E

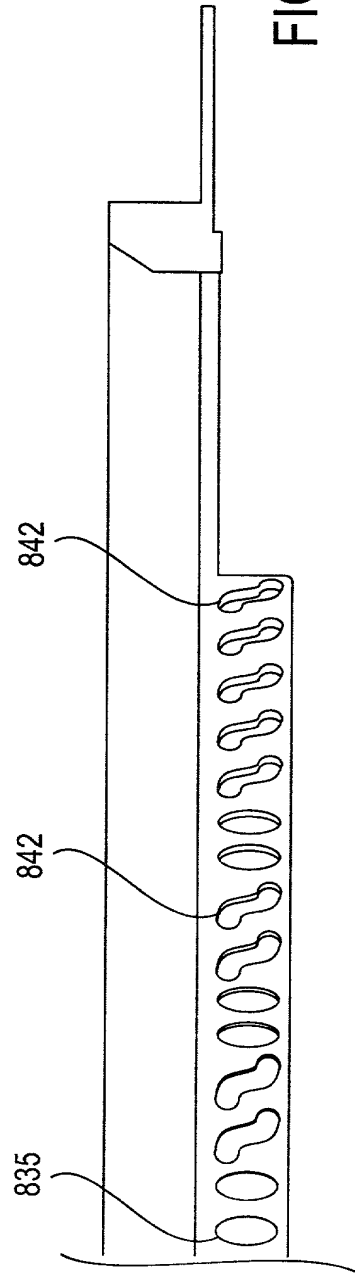


FIG. 8F

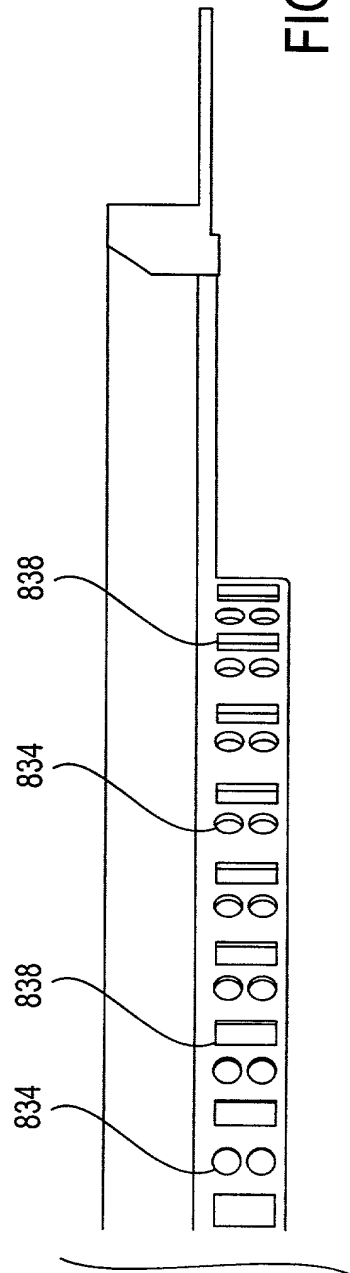


FIG. 8G

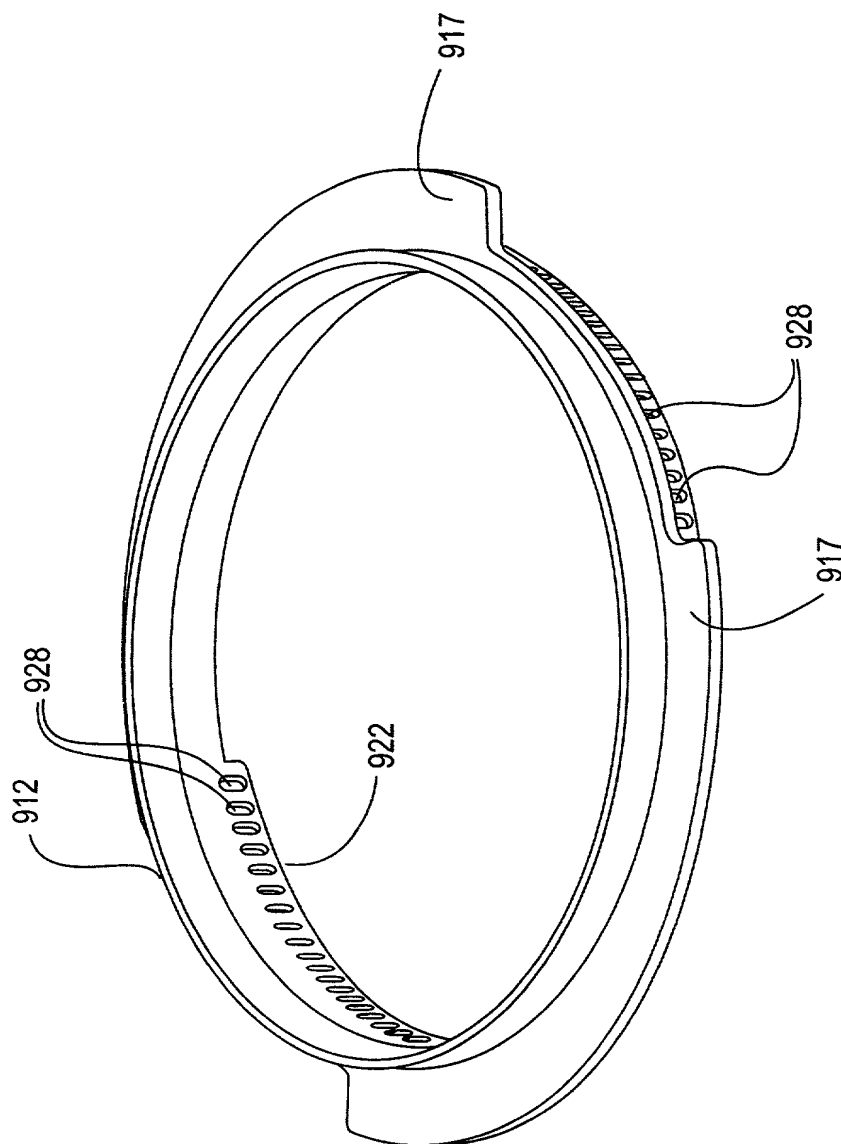


FIG. 9A

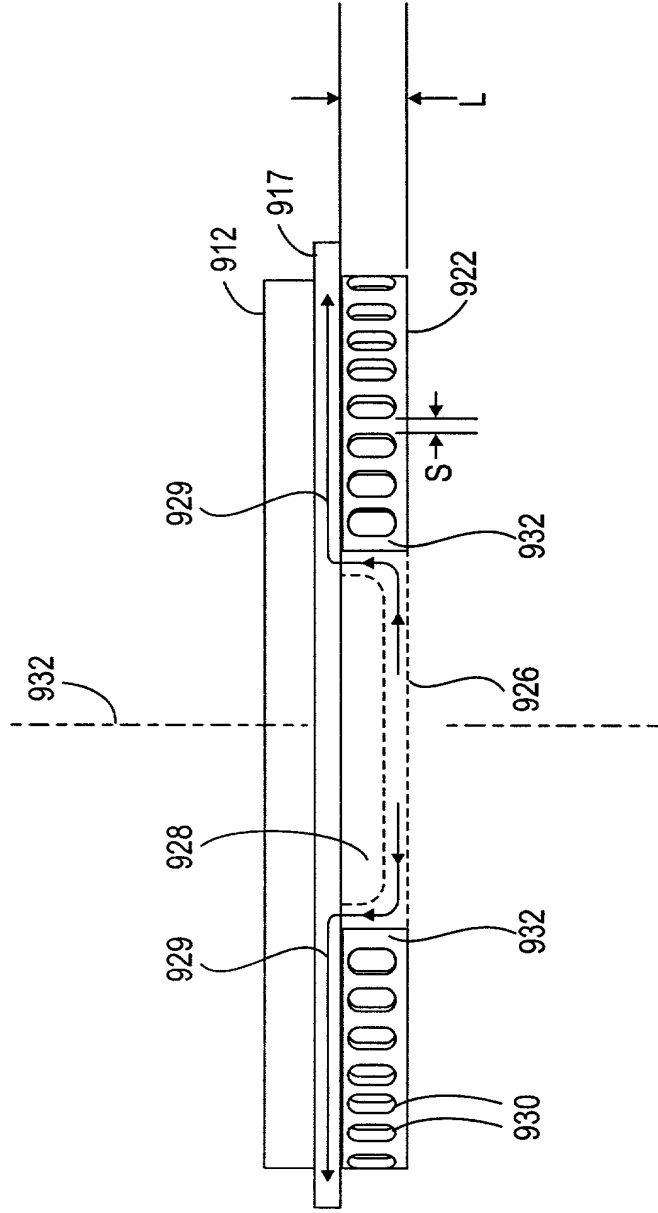


FIG. 9B

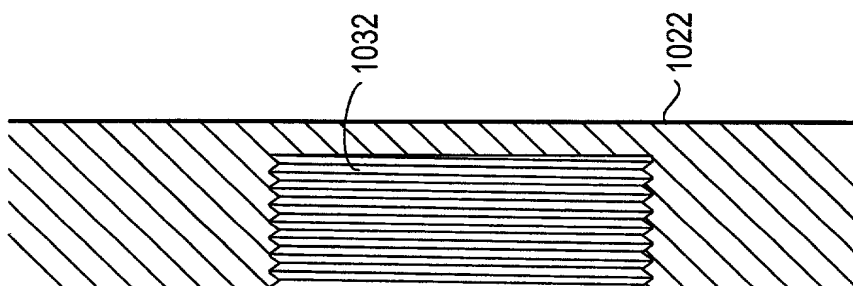


FIG. 10C

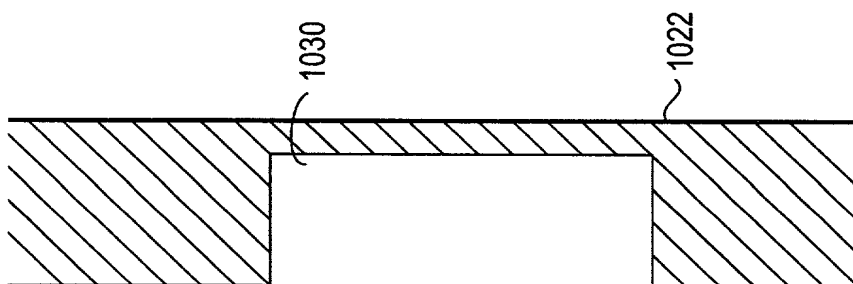


FIG. 10B

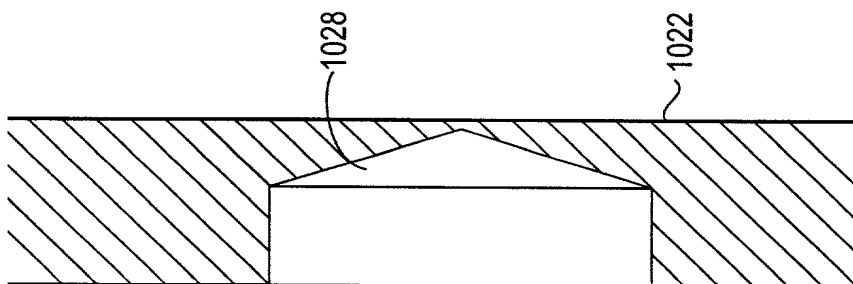


FIG. 10A